

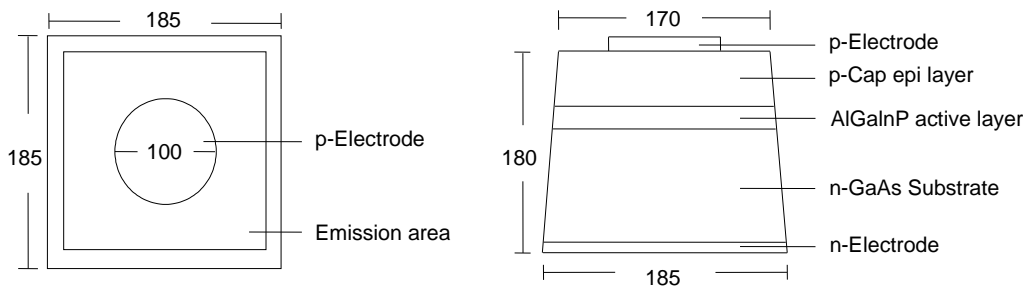
### ■ Features :

- MOVPE Epi Wafer
- Suitable for New Creative Products

### ■ Typical Applications :

- Dot Matrix
- Lamp Display
- High Performance X'mas Lamps

### ■ Outline Dimensions : (Unit: $\mu\text{m}$ )



### ■ Physical Structure :

Chip dimension	Chip size	185 $\mu\text{m}$ x 185 $\mu\text{m}$
	Thickness	180 $\mu\text{m}$
	Emission area	170 $\mu\text{m}$
	Bonding pad	100 $\mu\text{m}$
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

### ■ Electro-Optical Characteristics : ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20 \text{ mA}$	-	2.15	2.40	V
Reverse Voltage	$V_R$	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	$\lambda_p$	$I_F = 20 \text{ mA}$	-	573	-	nm
	$\lambda_D$		570	573	577	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Luminous Intensity	$I_V$	$I_F = 20 \text{ mA}$	25	-	-	mcd

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

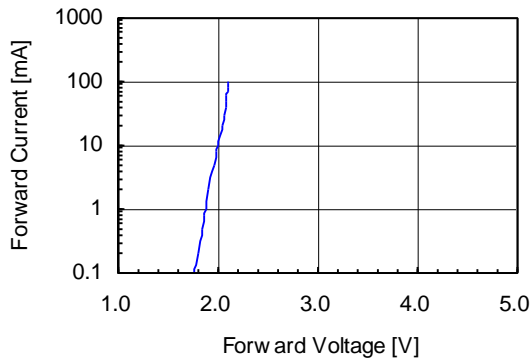


Fig 2. Relative Intensity vs. Forward Current

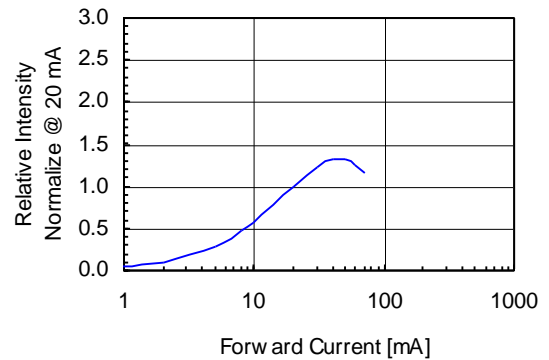


Fig 3. Forward Voltage vs. Temperature

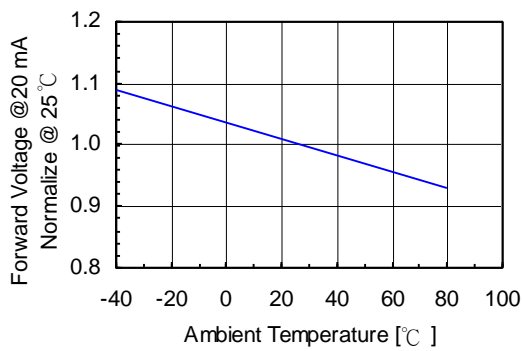


Fig 4. Relative Intensity vs. Temperature

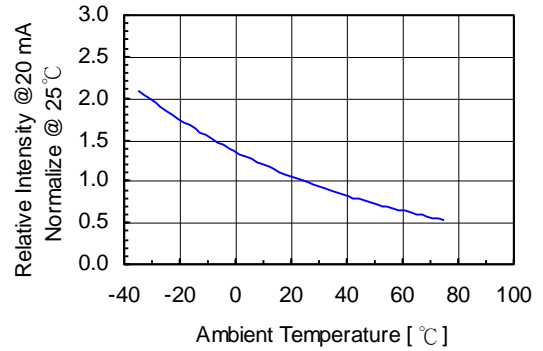


Fig 5. Relative Intensity vs. Wavelength

